# Complementary Silicon Transistors, Plastic, Medium-Power

# TIP100, TIP101, TIP102 (NPN); TIP105, TIP106, TIP107 (PNP)

Designed for general-purpose amplifier and low-speed switching applications.

#### Features

• High DC Current Gain -

 $h_{FE} = 2500 (Typ) @ I_C$ = 4.0 Adc

- Collector-Emitter Sustaining Voltage @ 30 mAdc
  - $V_{CEO(sus)} = 60 \text{ Vdc} (Min) \text{TIP100}, \text{TIP105}$ 
    - = 80 Vdc (Min) TIP101, TIP106
      - = 100 Vdc (Min) TIP102, TIP107
- Low Collector-Emitter Saturation Voltage -

$$V_{CE(sat)} = 2.0 \text{ Vdc} (Max) @ I_C$$

$$= 3.0 \, \text{Adc}$$

$$= 2.5 \text{ Vdc} (\text{Max}) @ I_{\text{C}} = 8.0 \text{ Adc}$$

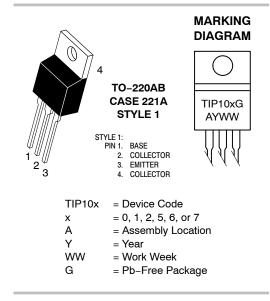
- Monolithic Construction with Built-in Base-Emitter Shunt Resistors
- These Devices are Pb-Free and are RoHS Compliant



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DARLINGTON 8 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60-80-100 VOLTS, 80 WATTS



#### ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

#### MAXIMUM RATINGS

Rating	Symbol	TIP100, TIP105	TIP101, TIP106	TIP102, TIP107	Unit		
Collector – Emitter Voltage	V <sub>CEO</sub>	60	80	100	Vdc		
Collector – Base Voltage	V <sub>CB</sub>	60	60 80 100		Vdc		
Emitter – Base Voltage	V <sub>EB</sub>	5.0			Vdc		
Collector Current – Continuous – Peak	IC	8.0 15			Adc		
Base Current	Ι <sub>Β</sub>	1.0			Adc		
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	80 0.64			W W/°C		
Unclamped Inductive Load Energy (1)	E	30			30		mJ
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	2.0 0.016			W W/°C		
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150			°C		

#### **THERMAL CHARACTERISTICS**

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	1.56	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1.  $I_C = 1.1 \text{ A}, L = 50 \text{ mH}, P.R.F. = 10 \text{ Hz}, V_{CC} = 20 \text{ V}, R_{BE} = 100 \Omega$ 

ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic		Min	Max	Unit
OFF CHARACTERISTICS				

Collector-Emitter Sustaining Voltage (1)		V <sub>CEO(sus)</sub>			Vdc
$(I_{\rm C} = 30 \text{ mAdc}, I_{\rm B} = 0)$	TIP100, TIP105	( )	60	_	
	TIP101, TIP106		80	_	
	TIP102, TIP107		100	-	
Collector Cutoff Current		I <sub>CEO</sub>			μAdc
(V <sub>CE</sub> = 30 Vdc, I <sub>B</sub> = 0)	TIP100, TIP105		_	50	
(V <sub>CE</sub> = 40 Vdc, I <sub>B</sub> = 0)	TIP101, TIP106		-	50	
(V <sub>CE</sub> = 50 Vdc, I <sub>B</sub> = 0)	TIP102, TIP107		-	50	
Collector Cutoff Current		I <sub>CBO</sub>			μAdc
(V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0)	TIP100, TIP105		-	50	
(V <sub>CB</sub> = 80 Vdc, I <sub>E</sub> = 0)	TIP101, TIP106		_	50	
$(V_{CB} = 100 \text{ Vdc}, I_E = 0)$	TIP102, TIP107		-	50	
Emitter Cutoff Current ( $V_{BE}$ = 5.0 Vdc, $I_{C}$ = 0)		I <sub>EBO</sub>	-	8.0	mAdo

#### **ON CHARACTERISTICS (1)**

DC Current Gain	h <sub>FE</sub>			-
$(I_{C} = 3.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$		1000	20,000	
(I <sub>C</sub> = 8.0 Adc, V <sub>CE</sub> = 4.0 Vdc)		200	-	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			Vdc
(I <sub>C</sub> = 3.0 Adc, I <sub>B</sub> = 6.0 mAdc)		-	2.0	
(I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 80 mAdc)		-	2.5	
Base-Emitter On Voltage (I <sub>C</sub> = 8.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	V <sub>BE(on)</sub>	-	2.8	Vdc
DYNAMIC CHARACTERISTICS				

Small–Signal Current Gain ( $I_C$ = 3.0 Adc, $V_{CE}$ = 4.0 Vdc, f = 1.0 MHz)	h <sub>fe</sub>	4.0	-	-
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz) TIP105, TIP1 TIP100, TIP1	, 05		300 200	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2%.

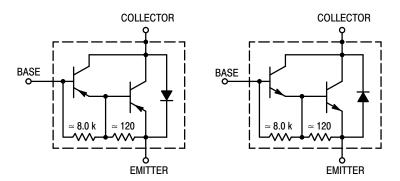
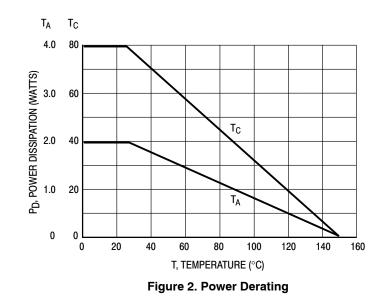


Figure 1. Darlington Circuit Schematic

#### **ORDERING INFORMATION**

Device	Package	Shipping
TIP100	TO-220	50 Units / Rail
TIP100G	TO-220 (Pb-Free)	50 Units / Rail
TIP101	TO-220	50 Units / Rail
TIP101G	TO-220 (Pb-Free)	50 Units / Rail
TIP102	TO-220	50 Units / Rail
TIP102G	TO-220 (Pb-Free)	50 Units / Rail
TIP105	TO-220	50 Units / Rail
TIP105G	TO-220 (Pb-Free)	50 Units / Rail
TIP106	TO-220	50 Units / Rail
TIP106G	TO-220 (Pb-Free)	50 Units / Rail
TIP107	TO-220	50 Units / Rail
TIP107G	TO-220 (Pb-Free)	50 Units / Rail



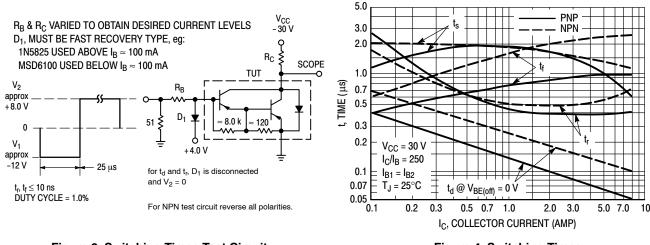


Figure 3. Switching Times Test Circuit

Figure 4. Switching Times

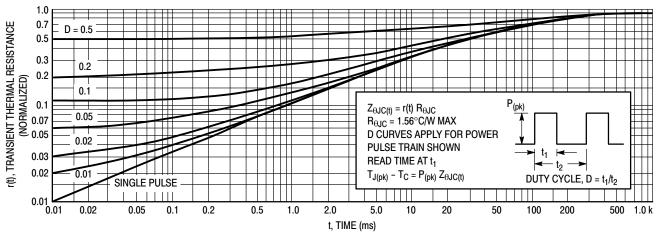


Figure 5. Thermal Response

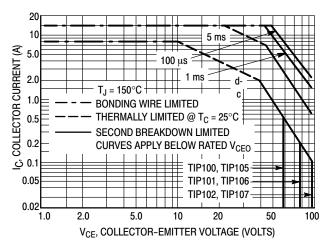


Figure 6. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150^{\circ}$ C;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)}$  < 150°C.  $T_{J(pk)}$  may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown

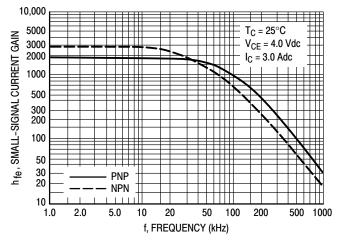
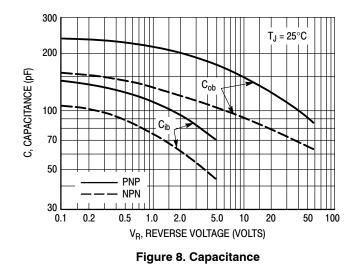
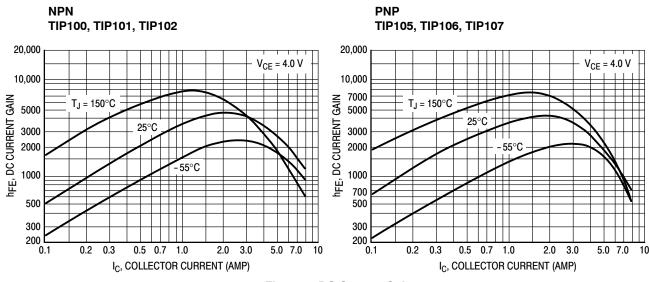


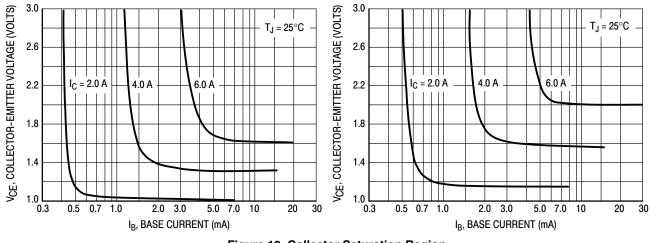
Figure 7. Small-Signal Current Gain



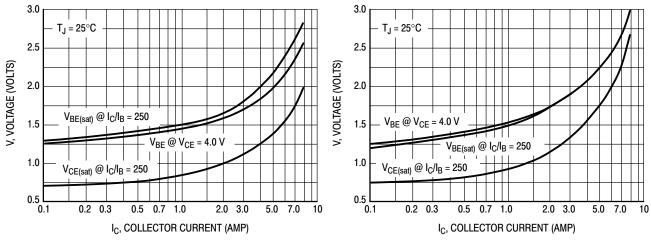
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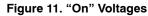












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